

**AMENDMENTS TO THE SPECIFICATION**

**Please amend the paragraph previously inserted with the filing of the Amendment under 37 C.F.R. § 1.114(c) filed January 14, 2010 (page 24, after line 19) of the specification:**

Fig. 5 is a cross-sectional view of a capacitor 1 produced in accordance with the method of the invention, including, as one electrode, an electric conductor 2 having formed on the surface thereof a dielectric layer 3 and, as the other part electrode, a semiconductor layer 4 formed on the electric conductor. Further, lead wire 7 is embedded in electric conductor 2. As shown in the enlarged view, feather-shaped fine protrusions 5 and other fine protrusions 6 are formed on the dielectric layer 3.

**Please insert the following paragraph before the heading "BEST MODE FOR CARRYING OUT THE INVENTION" on page 24 of the specification:**

Fig. 6 illustrates the energization of the embodiment of Example 1 for forming a semiconductor layer on sintered body 8, the sintered body 8 including lead wire 7 embedded in electric conductor 2 having formed on the surface thereof dielectric layer 3 and further including fine protrusions (not shown) formed on the dielectric layer 3. The sintered body 8 is dipped into electrolytic solution (semiconductor layer - forming solution) 11, and a positive terminal of direct current source 10 is electrically connected to the lead wire 7 and a negative terminal of the direct current source is electrically connected to a negative electrode plate 9 disposed in the electrolytic solution, to thereby pass a direct current between the lead wire 7 and the negative electrode plate 9.